

In the Specification

Please amend the title as follows:

Methods of Forming Semiconductor Circuitry, ~~and Semiconductor Constructions.~~

At page 1, before the "Technical Field" section, please insert the following paragraph:

RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/989,931, which was filed on November 21, 2001. ^{PAT 6,861,326}

Please amend paragraph [0040] on pages 12-13 as follows:

[0040] Fig. 8 is a top view of semiconductor construction 10, and diagrammatically illustrates a zonal configuration of one embodiment of the present invention. The construction of Fig. 8 is shown at a processing step corresponding to that of Fig. 6. Semiconductive material mass 30 extends around an exposed portion ~~50~~ 51 of monocrystalline material 16. In other words, upper surface 32 of mass 30 encircles the exposed portion ~~50~~ 51 of monocrystalline mass 16. Another exposed portion ~~52~~ 53 of mass 16 is shown outwardly of mass 30 relative to the encircled exposed portion ~~50~~ 51. The first semiconductor circuit component 36 of Fig. 7 can correspond to a portion of a DRAM array, and such DRAM array can be formed in the encircled exposed portion ~~50~~ 51 of monocrystalline mass 16. The second semiconductor circuit component 38 can correspond to a portion of circuitry formed peripheral to the DRAM array, and in the shown embodiment can correspond to a portion of circuitry which encircles the DRAM array. The